

## **isc Silicon NPN Power Transistor**

# 2SC5359

#### DESCRIPTION

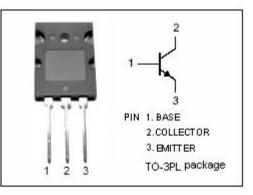
- High Current Capability
- High Power Dissipation
- High Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 230V(Min)
- Complement to Type 2SA1987
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

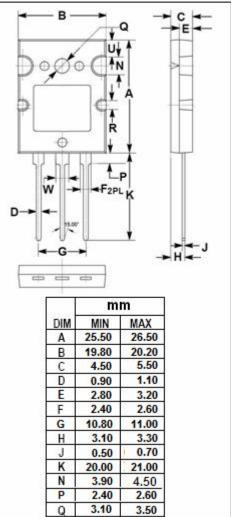
### APPLICATIONS

- Power amplifier applications
- Recommend for 100W high fidelity audio frequency
  amplifier output stage applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	230	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	230	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	15	A	
I <sub>B</sub>	Base Current-Continuous	1.5	A	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	180	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range -55~150 °C		°C	





isc Website: www.iscsemi.cn

1.90

3.90

2.90

2.60

4.10

3.25

R

U

W

1



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V(BR)CEO	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	230			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8.0A; I <sub>B</sub> = 0.8A			3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 230V; I <sub>E</sub> = 0			5	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	μA
hfe-1	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	55		160	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V	35			
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		200		pF
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		30		MHz

### h<sub>FE-1</sub> Classifications

R	0
55-110	80-160



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